

UNR1231 (UN1231), UNR1231A (UN1231A)

Silicon NPN epitaxial planar type

For amplification of the low frequency

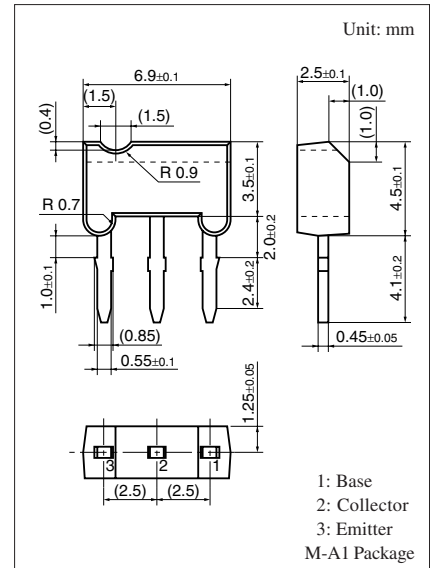
■ Features

- High forward current transfer ratio h_{FE}
- M type mold package
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

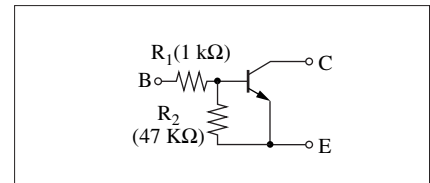
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	UNR1231 UNR1231A	V_{CBO} 20 60	V
Collector-emitter voltage (Base open)	UNR1231 UNR1231A	V_{CEO} 20 50	V
Collector current	I_C	0.7	A
Peak collector current	I_{CP}	1.5	A
Total power dissipation *	P_T	1.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



Internal Connection

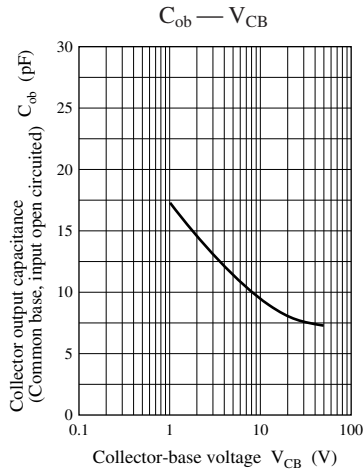
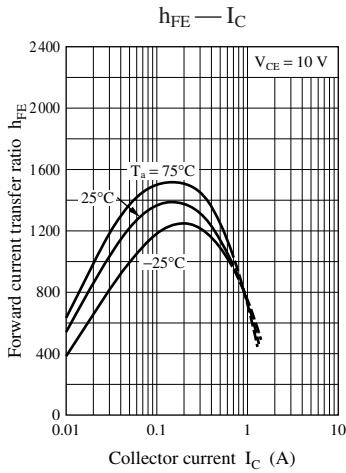
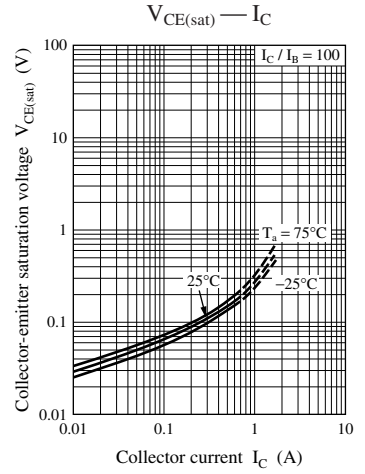
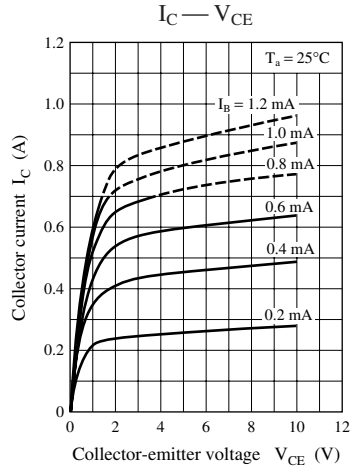
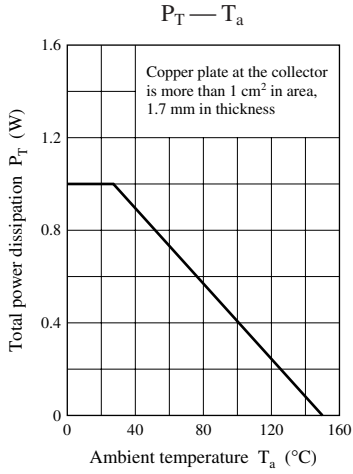
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	UNR1231 UNR1231A	V_{CBO} $I_C = 10 \mu\text{A}$, $I_E = 0$	20 60			V
Collector-emitter voltage (Base open)	UNR1231 UNR1231A	V_{CEO} $I_C = 1 \text{ mA}$, $I_B = 0$	20 50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 15 \text{ V}$, $I_E = 0$			1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 15 \text{ V}$, $I_B = 0$			10	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 14 \text{ V}$, $I_C = 0$			0.5	mA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10 \text{ V}$, $I_C = 150 \text{ mA}$	800	2 100		—
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 500 \text{ mA}$, $I_B = 5 \text{ mA}$			0.4	V
Transition frequency	f_T	$V_{CB} = 20 \text{ V}$, $I_E = -20 \text{ mA}$, $f = 200 \text{ MHz}$		55		MHz
Input resistance	R_1		0.7	1	1.3	V
Resistance ratio	R_1/R_2		0.016	0.021	0.025	—

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement

Note) The part numbers in the parenthesis show conventional part number.



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